

# Yong Tae Kim

## List of Publications by Year in descending order

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31  
papers

294  
citations

1163117

8  
h-index

888059

17  
g-index

31  
all docs

31  
docs citations

31  
times ranked

289  
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigation of electrical characteristics of the $\text{In}_{3-x}\text{Sb}_x\text{Te}_2$ ternary alloy for application in phase-change memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009, 3, 103-105.	2.4	62
2	A review of the Z 2 -FET 1T-DRAM memory: Operation mechanisms and key parameters. <i>Solid-State Electronics</i> , 2018, 143, 10-19.	1.4	36
3	Effects of excess Sb on crystallization of $\text{In}_{3-x}\text{Sb}_x\text{Te}_2$ phase SbTe binary thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 1636-1640.	1.8	24
4	Microstructures corresponding to multilevel resistances of $\text{In}_3\text{Sb}_1\text{Te}_2$ phase-change memory. <i>Applied Physics Letters</i> , 2011, 98, 091915.	3.3	24
5	Investigation of the structural transformation behavior of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ thin films using high resolution electron microscopy. <i>Applied Physics Letters</i> , 2007, 91, 101909.	3.3	22
6	Lattice Distortion in $\text{In}_3\text{SbTe}_2$ Phase Change Material with Substitutional Bi. <i>Scientific Reports</i> , 2015, 5, 12867.	3.3	17
7	Understanding of relationship between dopant and substitutional site to develop novel phase-change materials based on $\text{In}_3\text{SbTe}_2$ . <i>Japanese Journal of Applied Physics</i> , 2019, 58, SBBB02.	1.5	15
8	Atomic crystal structure of ordered $\text{In}_3\text{Sb}_1\text{Te}_2$ ternary alloy studied by high-resolution transmission electron microscopy. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	11
9	Pulse plasma assisted atomic layer deposition of W-C-N thin films for Cu interconnects. <i>Physica Status Solidi A</i> , 2005, 202, R164-R166.	1.7	8
10	Structural study on the crystallization behavior of $\text{Sb}_3\text{Te}_2$ alloy for phase change memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2007, 1, R25-R27.	2.4	7
11	Microstructural failure in $\text{Ge}_2\text{Sb}_2\text{Te}_5$ phase change memory cell. <i>Physica Status Solidi (B): Basic Research</i> , 2014, 251, 435-438.	1.5	7
12	Material design for $\text{Ge}_2\text{Sb}_2\text{Te}_5$ phase-change material with thermal stability and lattice distortion. <i>Scripta Materialia</i> , 2019, 170, 16-19.	5.2	7
13	The effect of carbon-doped $\text{In}_3\text{Sb}_1\text{Te}_2$ ternary alloys for multibit (MLC) phase-change memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 243-247.	2.4	6
14	The low temperature epitaxy of Ge on Si (1 0 0) substrate using two different precursors of $\text{GeH}_4$ and $\text{Ge}_2\text{H}_6$ . <i>Solid-State Electronics</i> , 2016, 124, 35-41.	1.4	6
15	Effects of Y Dopant on Lattice Distortion and Electrical Properties of $\text{In}_3\text{SbTe}_2$ Phase-Change Material. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1700275.	2.4	6
16	Characteristics of plasma enhanced chemical vapor deposited W-C-N thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2002, 20, 194-197.	2.1	5
17	A new atomic layer deposition of W-N thin films. <i>Physica Status Solidi A</i> , 2004, 201, R92-R95.	1.7	5
18	Interface-Driven Phase Transition of Phase-Change Material. <i>Crystal Growth and Design</i> , 2019, 19, 2123-2130.	3.0	5

#	ARTICLE	IF	CITATIONS
19	Mechanism of shear transformation in Ge <sup>2</sup> Bi <sup>2</sup> Te alloys. Physica Status Solidi - Rapid Research Letters, 2009, 3, 254-256.	2.4	4
20	Memory Operations of Zero Impact Ionization, Zero Subthreshold Swing FET Matrix Without Selectors. IEEE Electron Device Letters, 2020, 41, 361-364.	3.9	4
21	Nucleation, growth, and phase transformation mechanism of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> thin films. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 2542-2545.	1.8	3
22	Fabrication of MFISFETs with Pt/SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> /Y <sub>2</sub> O <sub>3</sub> /Si gate structure by developing an etch-stop process. Physica Status Solidi A, 2004, 201, R65-R68.	1.7	2
23	Characteristics of band modulation FET on sub 10 nm SOI. Japanese Journal of Applied Physics, 2019, 58, SBBB07.	1.5	2
24	Memory Operation of Z <sup>2</sup> -FET Without Selector at High Temperature. IEEE Journal of the Electron Devices Society, 2021, 9, 658-662.	2.1	2
25	Improved Retention Characteristics of Z <sup>2</sup> -FET Employing Half Back-Gate Control. IEEE Transactions on Electron Devices, 2021, 68, 1041-1044.	3.0	2
26	Improvement of ferroelectric properties of Pt <sup>2</sup> SrBi <sub>2</sub> Nb <sub>2</sub> O <sub>9</sub> <sup>2</sup> SiO <sub>2</sub> <sup>2</sup> Si gate structure through oxygen plasma rapid thermal annealing. Physica Status Solidi A, 2004, 201, 125-129.	1.7	1
27	Effects of an in vacancy on local distortion of fast phase transition in Bi-doped In <sub>3</sub> SbTe <sub>2</sub> . Journal of the Korean Physical Society, 2017, 71, 946-949.	0.7	1
28	Equivalent circuit model for the electrical analysis of a spin bipolar transistor. Physica Status Solidi A, 2004, 201, 808-814.	1.7	0
29	Lattice structural analysis of hydrogen induced defects in SrBi <sub>2</sub> Nb <sub>2</sub> O <sub>9</sub> thin films. Physica Status Solidi A, 2004, 201, R123-R126.	1.7	0
30	Influences of partial melting and overheating on amorphization of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> during the reset process. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2657-2661.	1.8	0
31	Effects of Y Dopant on Lattice Distortion and Electrical Properties of In <sub>3</sub> SbTe <sub>2</sub> Phase-Change Material (Phys. Status Solidi RRL 11/2017). Physica Status Solidi - Rapid Research Letters, 2017, 11, 1770356.	2.4	0